

**Ordering Information:****Absolute Maximum Ratings** $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	100	A
	$I_{D@TC=75}$	76	A
	$I_{D@TC=100}$	63	A
Pulsed Drain Current	I_{DM}	260	A
Total Power Dissipation($T_C=25$)	$P_D@TC=25$	85	W
Total Power Dissipation($T_A=25$)	$P_D@TA=25$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	



Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

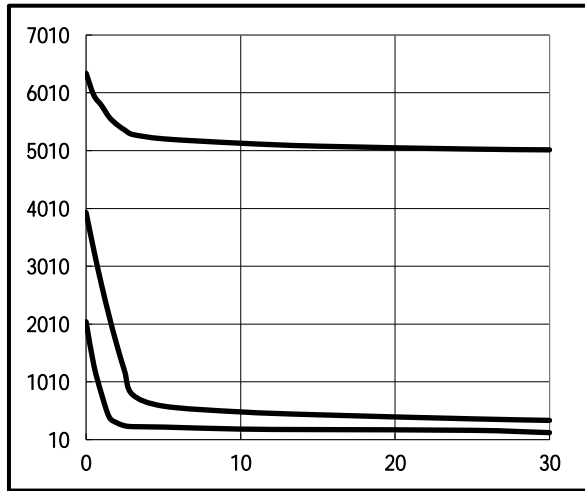




Fig.7 On-Resistance VS Gate Source Voltage

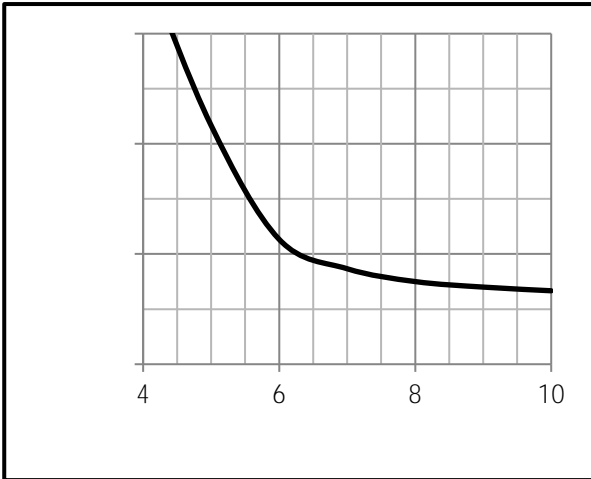


Fig.9 Switching Time Measurement Circuit

Fig.8 On-Resistance V.S Junction Temperature

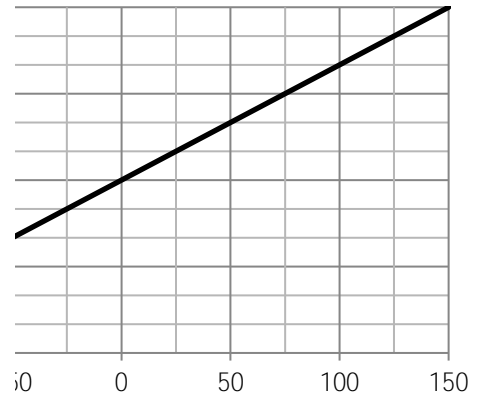


Fig.10 Gate Charge Waveform

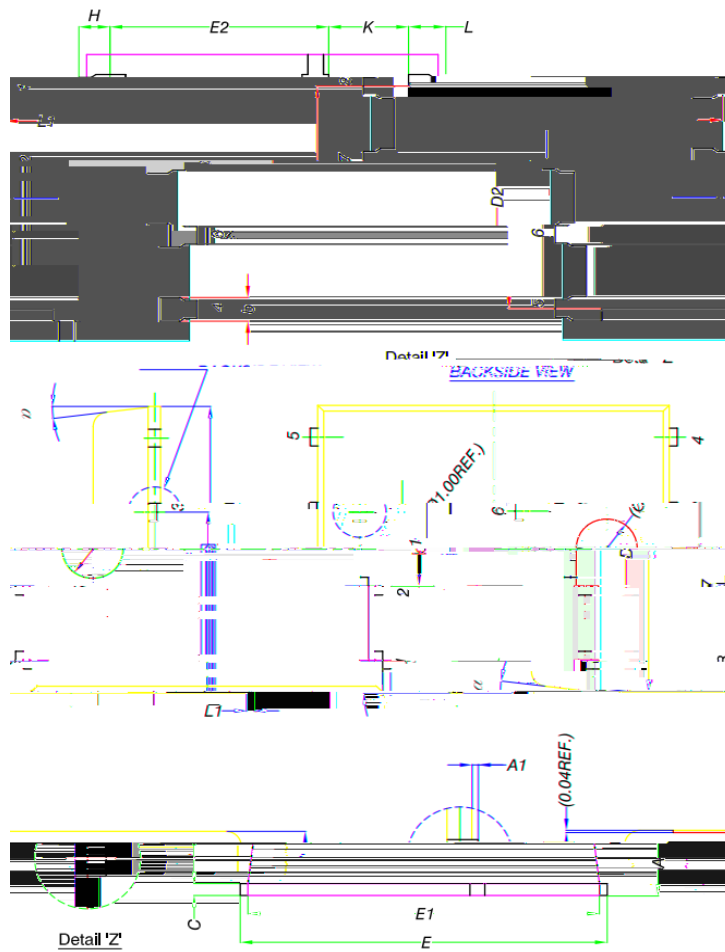
Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform



Dimensions DFN5x6

Unit mm



MILLIMETERS

D1	4.80	4.90	5.00
D2	3.67	3.81	3.96
	5.90	6.00	6.10
E1	5.20	5.28	5.36
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10		
L		0.51	0.61
L1		0.51	0.61
L2		0.51	0.61
			12°